Wen-Chau Liu

List of Publications by Year
in descending order

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151 papers	2,384 citations	201674 27 h-index	289244 40 g-index
151 all docs	151 docs citations	151 times ranked	1351 citing authors

#	Article	IF	Citations
1	Characteristics of a Pt/NiO thin film-based ammonia gas sensor. Sensors and Actuators B: Chemical, 2018, 256, 962-967.	7.8	104
2	Improved hydrogen sensing characteristics of a Pt/SiO2/GaN Schottky diode. Sensors and Actuators B: Chemical, 2008, 129, 292-302.	7.8	82
3	On the Ammonia Gas Sensing Performance of a RF Sputtered NiO Thin-Film Sensor. IEEE Sensors Journal, 2015, 15, 3711-3715.	4.7	76
4	Comparative study of hydrogen sensing characteristics of a Pd/GaN Schottky diode in air and N2 atmospheres. Sensors and Actuators B: Chemical, 2007, 123, 1040-1048.	7.8	73
5	Comparison of hydrogen sensing characteristics for Pd/GaN and Pd/Al0.3Ga0.7As Schottky diodes. Sensors and Actuators B: Chemical, 2006, 117, 151-158.	7.8	71
6	Hydrogen-sensitive characteristics of a novel Pd/InP MOS Schottky diode hydrogen sensor. IEEE Transactions on Electron Devices, 2001, 48, 1938-1944.	3.0	65
7	Formaldehyde sensing characteristics of an aluminum-doped zinc oxide (AZO) thin-film-based sensor. Sensors and Actuators B: Chemical, 2018, 255, 3017-3024.	7.8	57
8	Study of a WO3 thin film based hydrogen gas sensor decorated with platinum nanoparticles. Sensors and Actuators B: Chemical, 2020, 317, 128145.	7.8	50
9	Temperature-dependent characteristics of polysilicon and diffused resistors. IEEE Transactions on Electron Devices, 2003, 50, 1413-1415.	3.0	48
10	Characteristics of Pd/InGaP Schottky Diodes Hydrogen Sensors. IEEE Sensors Journal, 2004, 4, 72-79.	4.7	47
11	Improved temperature-dependent performances of a novel InGaP-InGaAs-GaAs double channel pseudomorphic high electron mobility transistor (DC-PHEMT). IEEE Transactions on Electron Devices, 2002, 49, 1687-1693.	3.0	44
12	Study of an electroless plating (EP)-based Pt/AlGaN/GaN Schottky diode-type ammonia sensor. Sensors and Actuators B: Chemical, 2014, 203, 258-262.	7.8	44
13	A Novel $hbox{Pt/In}_{0.52}hbox{Al}_{0.48}hbox{As}$ Schottky Diode-Type Hydrogen Sensor. IEEE Electron Device Letters, 2006, 27, 951-954.	3.9	41
14	On an Ammonia Gas Sensor Based on a Pt/AlGaN Heterostructure Field-Effect Transistor. IEEE Electron Device Letters, 2012, 33, 612-614.	3.9	40
15	Investigation of temperature-dependent characteristics of an n/sup +/-InGaAs/n-GaAs composite doped channel HFET. IEEE Transactions on Electron Devices, 2001, 48, 2677-2683.	3.0	39
16	A new Pd-oxide-Al/sub 0.3/Ga/sub 0.7/As MOS hydrogen sensor. IEEE Electron Device Letters, 2003, 24, 390-392.	3.9	38
17	A new Pt/oxide/In/sub 0.49/Ga/sub 0.51/P MOS Schottky diode hydrogen sensor. IEEE Electron Device Letters, 2002, 23, 640-642.	3.9	37
18	A novel InGaP/GaAs S-shaped negative-differential-resistance (NDR) switch for multiple-valued logic applications. IEEE Transactions on Electron Devices, 1997, 44, 520-525.	3.0	33

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19	Ammonia sensing characteristics of a Pt/AlGaN/GaN Schottky diode. Sensors and Actuators B: Chemical, 2011, 155, 347-350.	7.8	33
20	On a GaN-based ion sensitive field-effect transistor (ISFET) with a hydrogen peroxide surface treatment. Sensors and Actuators B: Chemical, 2015, 209, 658-663.	7.8	33
21	Investigation of hydrogen-sensing properties of Pd/AlGaAs-based Schottky diodes. IEEE Transactions on Electron Devices, 2003, 50, 2532-2539.	3.0	32
22	Influences of sulfur passivation on temperature-dependent characteristics of an AlGaAs/InGaAs/GaAs PHEMT. IEEE Transactions on Electron Devices, 2006, 53, 1-8.	3.0	32
23	SiO2 passivation effect on the hydrogen adsorption performance of a Pd/AlGaN-based Schottky diode. Sensors and Actuators B: Chemical, 2009, 136, 338-343.	7.8	32
24	On an AlGaInP-Based Light-Emitting Diode With an ITO Direct Ohmic Contact Structure. IEEE Electron Device Letters, 2009, 30, 359-361.	3.9	31
25	Ammonia Sensing Properties of a Pt/AlGaN/GaN Schottky Diode. IEEE Transactions on Electron Devices, 2011, 58, 1541-1547.	3.0	31
26	Comprehensive study on hydrogen sensing properties of a Pdâ€“AlGaN-based Schottky diode. International Journal of Hydrogen Energy, 2008, 33, 2986-2992.	7.1	30
27	Improved Light Extraction Efficiency of a High-Power GaN-Based Light-Emitting Diode With a Three-Dimensional-Photonic Crystal (3-D-PhC) Backside Reflector. IEEE Electron Device Letters, 2013, 34, 777-779.	3.9	30
28	Comprehensive study of a Pdâ€“GaAs high electron mobility transistor (HEMT)-based hydrogen sensor. Sensors and Actuators B: Chemical, 2007, 122, 81-88.	7.8	29
29	Hydrogen sensing characteristics of a Pd/AlGaOx/AlGaN-based Schottky diode. Sensors and Actuators B: Chemical, 2017, 246, 408-414.	7.8	29
30	Enhancement of hydrogen sensing performance of a GaN-based Schottky diode with a hydrogen peroxide surface treatment. Sensors and Actuators B: Chemical, 2015, 211, 303-309.	7.8	28
31	Improved Performance of an InGaN-Based Light-Emitting Diode With a p-GaN/n-GaN Barrier Junction. IEEE Journal of Quantum Electronics, 2011, 47, 755-761.	1.9	27
32	Influences of Surface Sulfur Treatments on the Temperature-Dependent Characteristics of HBTs. IEEE Transactions on Electron Devices, 2004, 51, 1963-1971.	3.0	24
33	Characteristics of a GaN-Based Light-Emitting Diode With an Inserted p-GaN/i-InGaN Superlattice Structure. IEEE Journal of Quantum Electronics, 2010, 46, 492-498.	1.9	24
34	Investigation of a new InGaP-InGaAs pseudomorphic double doped-channel heterostructure field-effect transistor (PDDCHFET). IEEE Transactions on Electron Devices, 2003, 50, 1717-1723.	3.0	23
35	Study of a New Field-Effect Resistive Hydrogen Sensor Based on a Pd/Oxide/AlGaAs Transistor. IEEE Transactions on Electron Devices, 2007, 54, 1224-1231.	3.0	23
36	Hydrogen sensing performance of a Pd nanoparticle/Pd film/GaN-based diode. Sensors and Actuators B: Chemical, 2017, 247, 514-519.	7.8	23

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37	Influence of channel doping-profile on camel-gate field effect transistors. IEEE Transactions on Electron Devices, 1996, 43, 871-876.	3.0	22
38	Investigation on a Pdâ€“AlGaN/GaN Schottky Diode-Type Hydrogen Sensor With Ultrahigh Sensing Responses. IEEE Transactions on Electron Devices, 2008, 55, 3575-3581.	3.0	22
39	Implementation of an indium-tin-oxide (ITO) direct-Ohmic contact structure on a GaN-based light emitting diode. Optics Express, 2011, 19, 14662.	3.4	22
40	Ammonia Sensing Characteristics of a Tungsten Trioxide Thin-Film-Based Sensor. IEEE Transactions on Electron Devices, 2019, 66, 696-701.	3.0	22
41	Study of a High-Performance Chemoresistive Ethanol Gas Sensor Synthesized With Au Nanoparticles and an Amorphous IGZO Thin Film. IEEE Transactions on Electron Devices, 2021, 68, 753-760.	3.0	22
42	Temperature-dependent study of a lattice-matched InP/InGaAlAs heterojunction bipolar transistor. IEEE Electron Device Letters, 2000, 21, 524-527.	3.9	20
43	Study of a Platinum (Pt) Nanoparticle (NP)/Vanadium Pentoxide (V₂O₅) Thin Film-Based Ammonia Gas Sensor. IEEE Transactions on Electron Devices, 2020, 67, 2126-2132.	3.0	20
44	Temperature-dependent investigation of a high-breakdown voltage and low-leakage current Ga/sub 0.51/In/sub 0.49/P/In/sub 0.15/Ga/sub 0.85/As pseudomorphic HEMT. IEEE Electron Device Letters, 1999, 20, 274-276.	3.9	19
45	On a GaN-Based Light-Emitting Diode With a p-GaN/i-InGaN Superlattice Structure. IEEE Electron Device Letters, 2009, 30, 1149-1151.	3.9	19
46	Investigation of Hydrogen-Sensing Characteristics of a Pd/GaN Schottky Diode. IEEE Sensors Journal, 2011, 11, 1194-1200.	4.7	19
47	Hydrogen sensing properties of a Pd/SiO2/AlGaN-based MOS diode. Electrochemistry Communications, 2009, 11, 65-67.	4.7	18
48	Ammonia Sensing Characteristics of Sputtered Indium Tin Oxide (ITO) Thin Films on Quartz and Sapphire Substrates. IEEE Transactions on Electron Devices, 2011, 58, 4407-4413.	3.0	18
49	A High-Performance Pd Nanoparticle (NP)/WO₃ Thin-Film-Based Hydrogen Sensor. IEEE Electron Device Letters, 2019, 40, 1194-1197.	3.9	18
50	Characterization of polysilicon resistors in sub-0.25 Î¼m CMOS ULSI applications. IEEE Electron Device Letters, 2001, 22, 318-320.	3.9	17
51	Hydrogen-Sensing Properties of a Pd/AlGaN/GaN-Based Field-Effect Transistor Under a Nitrogen Ambience. IEEE Sensors Journal, 2013, 13, 1787-1793.	4.7	17
52	Enhancement of Hydrogen Sensing Performance of a Pd Nanoparticle/Pd Film/GaO_{<italic>x</italic>}/GaN-Based Metalâ€“Oxideâ€“ Semiconductor Diode. IEEE Transactions on Electron Devices, 2018, 65, 4577-4584.	3.0	17
53	Study of a platinum nanoparticle (Pt NP)/amorphous In-Ga-Zn-O (A-IGZO) thin-film-based ammonia gas sensor. Sensors and Actuators B: Chemical, 2020, 322, 128592.	7.8	17
54	Ammonia Gas Sensing Performance of an Indium Tin Oxide (ITO) Based Device with an Underlying Au-Nanodot Layer. Journal of the Electrochemical Society, 2013, 160, B17-B22.	2.9	16

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55	New Room Temperature Ammonia Gas Sensor Synthesized by a Tantalum Pentoxide (Ta₂O₅) Dielectric and Catalytic Platinum (Pt) Metals. IEEE Transactions on Electron Devices, 2020, 67, 2566-2572.	3.0	16
56	Study of a New Hydrogen Gas Sensor Synthesized With a Sputtered Cerium Oxide Thin Film and Evaporated Palladium Nanoparticles. IEEE Transactions on Electron Devices, 2021, 68, 4077-4083.	3.0	16
57	Effects of the Use of an Aluminum Reflecting and an ${m SiO}_{2}$ Insulating Layers (RIL) on the Performance of a GaN-Based Light-Emitting Diode With the Naturally Textured p-GaN Surface. IEEE Transactions on Electron Devices, 2013, 60, 2282-2289.	3.0	15
58	Study of GaN-Based LEDs With Hybrid SiO₂ Microsphere/Nanosphere AntiReflection Coating as a Passivation Layer by a Rapid Convection Deposition. IEEE Transactions on Electron Devices, 2017, 64, 1134-1139.	3.0	15
59	Light Extraction Enhancement of GaN-Based Light-Emitting Diodes With Textured Sidewalls and ICP-Transferred Nanohemispherical Backside Reflector. IEEE Transactions on Electron Devices, 2017, 64, 3672-3677.	3.0	15
60	Formaldehyde Sensing Characteristics of a NiO-Based Sensor Decorated With Pd Nanoparticles and a Pd Thin Film. IEEE Transactions on Electron Devices, 2018, 65, 1956-1961.	3.0	15
61	Temperature-dependence investigation of a high-performance inverted delta-doped V-shaped GaInP/In/sub x/Ga/sub 1-x/As/GaAs pseudomorphic high electron mobility transistor. IEEE Transactions on Electron Devices, 2001, 48, 1290-1296.	3.0	14
62	Nitrogen Oxide (NO₂) Gas Sensing Performance of ZnO Nanoparticles (NPs)/Sapphire-Based Sensors. IEEE Sensors Journal, 2015, 15, 3759-3763.	4.7	14
63	Enhanced Light Extraction of a High-Power GaN-Based Light-Emitting Diode With a Nanohemispherical Hybrid Backside Reflector. IEEE Transactions on Electron Devices, 2015, 62, 3296-3301.	3.0	13
64	Enhanced Light Extraction of GaN-Based Light-Emitting Diodes With a Hybrid Structure Incorporating Microhole Arrays and Textured Sidewalls. IEEE Transactions on Electron Devices, 2018, 65, 3305-3310.	3.0	13
65	A Highly Sensitive Ammonia (NH₃) Sensor Based on a Tungsten Trioxide (WO₃) Thin Film Decorated With Evaporated Platinum (Pt) Nanoparticles. IEEE Transactions on Electron Devices, 2020, 67, 1176-1182.	3.0	13
66	Further Suppression of Surface-Recombination of an InGaP/GaAs HBT by Conformal Passivation. IEEE Transactions on Electron Devices, 2006, 53, 2901-2907.	3.0	12
67	Study of a Palladium (Pd)/Aluminum-Doped Zinc Oxide (AZO) Hydrogen Sensor and the Kalman Algorithm for Internet-of-Things (IoT) Application. IEEE Transactions on Electron Devices, 2020, 67, 4405-4412.	3.0	12
68	Hydrogen sensing properties of a novel GaN/AlGaN Schottky diode decorated with palladium nanoparticles and a platinum thin film. Sensors and Actuators B: Chemical, 2021, 330, 129339.	7.8	12
69	Multiple-route and multiple-state current-voltage characteristics of an InP/AlInGaAs switch for multiple-valued logic applications. IEEE Transactions on Electron Devices, 2000, 47, 1553-1559.	3.0	11
70	DC characterization of an InP-InGaAs tunneling emitter bipolar transistor (TEBT). IEEE Transactions on Electron Devices, 2003, 50, 874-879.	3.0	11
71	On an Electroless Plating (EP)-Based Pd/AlGaN/GaN Heterostructure Field-Effect Transistor (HFET)-Type Hydrogen Gas Sensor. IEEE Electron Device Letters, 2012, 33, 788-790.	3.9	11
72	Performance Improvement of GaN-Based Light-Emitting Diodes With a Microhole Array, 45Â° Sidewalls, and a SiO₂ Nanoparticle/Microsphere Passivation Layer. IEEE Transactions on Electron Devices, 2019, 66, 505-511.	3.0	11

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73	Ammonia Sensing Characteristics of a Platinum (Pt) Hybrid Structure/GaN-Based Schottky Diode. IEEE Transactions on Electron Devices, 2020, 67, 296-303.	3.0	11
74	A new and improved borderless contact (BLC) structure for high-performance Ti-salicide in sub-quarter micron CMOS devices. IEEE Electron Device Letters, 2000, 21, 344-346.	3.9	10
75	Characteristics of an AlGaInP-Based Light Emitting Diode With an Indium-Tin-Oxide (ITO) Direct Ohmic Contact Structure. IEEE Journal of Quantum Electronics, 2010, 46, 246-252.	1.9	10
76	Hydrogen Sensing Characteristics of a Metalâ€“Oxideâ€“Semiconductor Diode With Bimetallic Catalysts and a GaO x Dielectric. IEEE Transactions on Electron Devices, 2019, 66, 3144-3150.	3.0	10
77	On the multiple negative-differential-resistance (MNDR) InGaP-GaAs resonant tunneling bipolar transistors. IEEE Transactions on Electron Devices, 2001, 48, 1054-1059.	3.0	9
78	On the Pseudomorphic High Electron Mobility Transistors (PHEMTs) With a Low-Temperature Gate Approach. IEEE Electron Device Letters, 2009, 30, 325-327.	3.9	9
79	Comprehensive Temperature-Dependent Studies of Metamorphic High Electron Mobility Transistors With Double and Single $delta$-Doped Structures. IEEE Transactions on Electron Devices, 2011, 58, 4276-4282.	3.0	9
80	On a GaN-Based Light-Emitting Diode With an Aluminum Metal Mirror Deposited on Naturally-Textured V-Shaped Pits Grown on the p-GaN Surface. IEEE Electron Device Letters, 2012, 33, 227-229.	3.9	9
81	Study of a GaN-Based LED With an Al/AZO Composite Transparent Conductive Layer. IEEE Transactions on Electron Devices, 2017, 64, 3678-3682.	3.0	9
82	Hydrogen sensing properties of a GaN/AlGaN-based Schottky diode with a catalytic platinum (Pt) hybrid structure. Sensors and Actuators B: Chemical, 2021, 331, 129320.	7.8	9
83	Ammonia sensing characteristics of a cerium oxide thin film coated with platinum nanoparticles. Sensors and Actuators B: Chemical, 2022, 369, 132241.	7.8	9
84	A novel InP/InGaAs TEBT for ultralow current operations. IEEE Electron Device Letters, 2003, 24, 126-128.	3.9	8
85	Investigation of the Electrostatic Discharge Performance of GaN-Based Light-Emitting Diodes With Naturally Textured p-GaN Contact Layers Grown on Miscut Sapphire Substrates. IEEE Transactions on Electron Devices, 2010, 57, 2155-2162.	3.0	8
86	Hydrogen-Sensing Characteristics of a Pd/GaN Schottky Diode With a Simple Surface Roughness Approach. IEEE Transactions on Electron Devices, 2011, 58, 4079-4086.	3.0	8
87	Improved current spreading performance of a GaN-based light-emitting diode with a stair-like ITO layer. Solid-State Electronics, 2014, 99, 21-24.	1.4	8
88	Characteristics of GaN-Based LEDs With Hybrid Microhole Arrays and SiO₂Microspheres/Nanoparticles Structures. IEEE Transactions on Electron Devices, 2017, 64, 2854-2858.	3.0	8
89	Implementation of light extraction improvements of GaN-based light-emitting diodes with specific textured sidewalls. Optics and Laser Technology, 2018, 101, 172-176.	4.6	8
90	Influences of Microhole Depth and SiO₂ Nanoparticle/Microsphere Passivation Layer on the Performance of GaN-Based Light-Emitting Diodes. IEEE Transactions on Electron Devices, 2019, 66, 4211-4215.	3.0	8

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91	Study of a Palladium Nanoparticle/Indium Oxide-Based Hydrogen Gas Sensor. IEEE Transactions on Electron Devices, 2022, 69, 318-324.	3.0	8
92	Multiple-route current-voltage (I-V) characteristics of GaAs-InGaAs metal-insulator-semiconductor-like (MIS) structure for multiple-valued logic applications. IEEE Journal of Quantum Electronics, 1996, 32, 1615-1619.	1.9	7
93	InGaP/GaAs superlattice-emitter resonant tunneling bipolar transistor (SE-RTBT). IEEE Electron Device Letters, 1997, 18, 515-517.	3.9	7
94	On a GaN-Based Light-Emitting Diode With an Indiumâ€“Tinâ€“Oxide (ITO) Direct-Ohmic Contact Structure. IEEE Photonics Technology Letters, 2011, 23, 1037-1039.	2.5	7
95	On the temperature-dependent characteristics of a Pd/InAlAs based electroless-plating gate metamorphic heterostructure field-effect transistor (MHFET). Solid-State Electronics, 2013, 79, 50-55.	1.4	7
96	Study of a GaN-Based Light-Emitting Diode With a Gaâ„Oâ‚ƒ Current Blocking Layer and a Gaâ„Oâ‚ƒ Surface Passivation Layer. IEEE Transactions on Electron Devices, 2021, 68, 3894-3900.	3.0	7
97	Multiple negative-differential-resistance (NDR) of InGaP/GaAs heterostructure-emitter bipolar transistor (HEBT). IEEE Electron Device Letters, 1996, 17, 130-132.	3.9	6
98	The Effect of Sulfur Treatment on the Temperature-Dependent Performance of InGaP/GaAs HBTs. IEEE Transactions on Device and Materials Reliability, 2006, 6, 500-508.	2.0	6
99	A New InP/InGaAs Double Heterojunction Bipolar Transistor With a Step-Graded InAlGaAs Collector Structure. IEEE Electron Device Letters, 2008, 29, 11-14.	3.9	6
100	A novel InP/InAlGaAs negative-differential-resistance heterojunction bipolar transistor (NDR-HBT) with interesting topee-shaped current-voltage characteristics. IEEE Electron Device Letters, 1999, 20, 510-513.	3.9	5
101	Room-Temperature Hydrogen- and Ammonia Gas-Sensing Characteristics of a GaN-Based Schottky Diode Synthesized With a Hybrid Surface Structure. IEEE Transactions on Electron Devices, 2021, 68, 761-768.	3.0	5
102	Study of a Highly Sensitive Formaldehyde Sensor Prepared With a Tungsten Trioxide Thin Film and Gold Nanoparticles. IEEE Transactions on Electron Devices, 2021, 68, 6422-6429.	3.0	5
103	Hydrogen Sensing Properties of a Tin Dioxide Thin Film Incorporated with Evaporated Palladium Nanoparticles. ECS Journal of Solid State Science and Technology, 2022, 11, 027001.	1.8	5
104	Characteristics of an InPâ€“InGaAsâ€“InGaAsP HBT. IEEE Transactions on Electron Devices, 2004, 51, 1935-1938.	3.0	4
105	Effect of Nonannealed Ohmic-Recess Structure on Temperature-Dependent Characteristics of Metamorphic High-Electron-Mobility Transistors. Journal of the Electrochemical Society, 2008, 155, H443.	2.9	4
106	Performance Enhancement of GaN-Based Light-Emitting Diodes by Using Transparent Ag Metal Line Patterns. IEEE Transactions on Electron Devices, 2017, 64, 2542-2548.	3.0	4
107	Study of a Formaldehyde Gas Sensor Based on a Sputtered Vanadium Pentoxide Thin Film Decorated with Gold Nanoparticles. ECS Journal of Solid State Science and Technology, 2021, 10, 087001.	1.8	4
108	Hydrogen Sensing Properties of an Aluminum-Doped Zinc Oxide Layer Decorated With Palladium Nanoparticles. IEEE Electron Device Letters, 2022, 43, 280-283.	3.9	4

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109	A novel double ion-implant (DII) Ti-salicide technology for high-performance sub-0.25-Î¼m CMOS devices applications. IEEE Transactions on Electron Devices, 2001, 48, 1740-1742.	3.0	3
110	A new and improved structure of polysilicon resistor for subquarter micrometer CMOS device applications. IEEE Transactions on Electron Devices, 2003, 50, 516-518.	3.0	3
111	Characteristics of a double-barrier-emitter triangular-barrier ptoelectronic switch (DTOS). , 0, , .		3
112	A Wireless-Transfer-Based Hydrogen Gas Sensing System With a Pd/AlGaN/GaN Heterostructure Field-Effect Transistor (HFET). IEEE Sensors Journal, 2013, 13, 2299-2304.	4.7	3
113	Comparative study of InP/InGaAs double heterojunction bipolar transistors with InGaAsP spacer at base-collector junction. Semiconductors, 2013, 47, 1391-1396.	0.5	3
114	A Double-Barrier-Emitter Triangular-Barrier Optoelectronic Switch. IEEE Journal of Quantum Electronics, 2004, 40, 413-419.	1.9	2
115	Emitter-Induced Gain Effects on Dual-Emitter Phototransistor as an Electrooptical Switch. IEEE Transactions on Electron Devices, 2007, 54, 2411-2417.	3.0	2
116	Temperature-Dependent Characteristics of a Pseudomorphic High Electron Mobility Transistor with Graded Triple Delta-Doped Sheets. Journal of the Electrochemical Society, 2008, 155, H995.	2.9	2
117	On an AlGaInP Light-Emitting Diode With a Modulation-Doped Multiquantum-Well (MD-MQW) Structure. IEEE Journal of Quantum Electronics, 2009, 45, 367-372.	1.9	2
118	Study of GaN-Based Light-Emitting Diode (LED) With a Hybrid Surface Structure. IEEE Transactions on Electron Devices, 2020, 67, 4953-4957.	3.0	2
119	Temperature-Dependent Study of AlGaAs/InGaAs Integrated Depletion/Enhancement-Mode High Electron Mobility Transistors with Virtual Channel Layers. ECS Journal of Solid State Science and Technology, 2020, 9, 055019.	1.8	2
120	Study of a GaN-Based Light-Emitting Diode with a Specific Hybrid Structure. ECS Journal of Solid State Science and Technology, 2021, 10, 045001.	1.8	2
121	Inverter Logic of AlGaAs/InGaAs Enhancement/Depletion-Mode Pseudomorphic High Electron Mobility Transistors with Virtual Channel Layers. ECS Journal of Solid State Science and Technology, 2019, 8, Q211-Q216.	1.8	2
122	A new functional AlGaAs/InGaAs/GaAs heterostructure-emitter and heterostructure-base transistor (HEHBT). , 0, , .		1
123	Characteristics of a New BBOS With an AlGaAsâ€“<tex>$delta (rm n^+)$</tex>â€“GaAsâ€“InAlGaP Collector Structure. IEEE Transactions on Electron Devices, 2004, 51, 542-547.	3.0	1
124	Influence of emitter ledge width on the characteristics of InGaP/GaAs heterojunction bipolar transistors. , 2008, , .		1
125	An Improved GaN-Based Light-Emitting Diode with a SiO₂Current Blocking Layer Embedded in Stair-Like AZO Transparent Structure. ECS Journal of Solid State Science and Technology, 2017, 6, R149-R153.	1.8	1
126	Study of GaN/InGaN Light-Emitting Diodes with Specific Zirconium Oxide (ZrO₂) Layers. ECS Journal of Solid State Science and Technology, 2022, 11, 075003.	1.8	1

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127	Modeling and Simulating the Electrical Properties of Heterostructure-Emitter Bipolar Transistors. , 0, , .		0
128	Investigation of GaAs Doping Superlattice Structure. , 0, , .		0
129	GaAs Bipolar Transistor with a Triple-Well Emitter Structure. , 0, , .		0
130	Three-terminal switching device with InGaAs/GaAs/InGaAs hole confinement layer. , 0, , .		0
131	GaAs tri-step high-low doping channel field effect transistor. , 0, , .		0
132	Investigation of step-doped channel heterostructure field-effect transistor. , 0, , .		0
133	AlInAs/InGaAs long-period-superlattice resonant-tunneling transistor (LPSRTT) prepared by MOCVD. , 0, , .		0
134	Observation of the multiple negative-differential-resistance of metal-insulator-semiconductor-like structure with step-compositioned In/sub x/Ga/sub 1-x/As quantum wells. IEEE Electron Device Letters, 1997, 18, 129-131.	3.9	0
135	AlInAs/GaInAs superlatticed negative-differential-resistance switch (SNDRS) prepared by MOCVD. , 0, , .		0
136	A new InGaP-GaAs double delta-doped heterojunction bipolar transistor (D/sup 3/HBT). , 0, , .		0
137	MOCVD grown AlInAs/GaInAs short-period-superlattice resonant-tunneling transistor(SPSRTT). , 0, , .		0
138	InP/InGaAs heterojunction bipolar transistors with superlattice emitter structure. , 0, , .		0
139	High-performance n/sup +/-GaAs/p/sup +/-In/sub 0.49/Ga/sub 0.51/P/n-GaAs high-barrier gate heterostructure field-effect transistor. , 0, , .		0
140	Temperature-dependent characteristics of InP/In/sub 0.53/Ga/sub 0.34/Al/sub 0.13/As heterojunction bipolar transistor. , 0, , .		0
141	Numerical and experimental analsis of an InP/InGaAs tunneling emitter bipolar transistor (TEBT) for low-voltage and low-power circuit applications. , 0, , .		0
142	A High-Sensitive Pd/InGaP transistor hydrogen sensor. , 2007, , .		0
143	A Pt/GaN Schottky diode-type hydrogen sensor with a thin SiO<inf>2</inf>-passivated metal/semiconductor junction. , 2008, , .		0
144	A Pd/Oxide/AlGaAs (MOS) junction resistor-type hydrogen sensor. , 2008, , .		0

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145	Investigation of InP/InGaAs Double Heterojunction Bipolar Transistor (DHBT) with a step-graded InAlGaAs/InP collector structure. , 2008, , .		0
146	Ethanol vapor sensors based on carboxyl- alkanethiolate self-assembled monolayers modified Au/GaAs Schottky diodes. , 2009, , .		0
147	An optoelectronic switch. , 2009, , .		0
148	Influence of gate-to-source and gate-to-drain recesses on GaAs camel-like gate field-effect transistors. Semiconductors, 2014, 48, 1222-1225.	0.5	0
149	Hydrogen sensing performance of an electrophoretic deposition (EPD) based Pd/GaN Schottky diode. , 2015, , .		0
150	Comparative Study of AlGaN/AlN/GaN Metal-Oxide-Semiconductor High Electron Mobility Transistors with Ni/Au Gate Electrode. ECS Journal of Solid State Science and Technology, 0, , .	1.8	0
151	Pd Nanoparticle/Pd/Al2O3 Resistive Sensor for Hydrogen Detection in a High-Temperature Environment. ECS Journal of Solid State Science and Technology, 0, , .	1.8	0